Transistors

## 2SB1030A

### Silicon PNP epitaxial planar type

For low-frequency amplification Complementary to 2SD1423A

#### ■ Features

- Optimum for high-density mounting
- Allowing supply with the radial taping

#### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-60	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-50	V	
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	-7	V	
Collector current	$I_{C}$	-0.5	A	
Peak collector current	$I_{CP}$	-1	A	
Collector power dissipation	P <sub>C</sub>	300	mW	
Junction temperature	T <sub>j</sub>	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C ,	

#### ■ Package

- Code
  - NS-B1
- Pin Name
  - 1. Emitter
  - 2. Collector
  - 3. Base

#### ■ Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_{\rm C} = -10 \mu\text{A}, I_{\rm E} = 0$	-60	100		V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50	O()		V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = -10 \mu\text{A}, I_C = 0$	-7			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -20 \text{ V}, I_{E} = 0$	60.		-0.1	μΑ
Collector-Emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = -20 \text{ V}, I_{B} = 0$			-1	μΑ
Forward current transfer ratio	h <sub>FE1</sub> *	$V_{CE} = -10 \text{ V}, I_{C} = -150 \text{ mA}$	85		340	
	h <sub>FE2</sub>	$V_{CE} = -10 \text{ V}, I_{C} = -500 \text{ A}$	40			_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = -300 \text{ mA}, I_B = -30 \text{ mA}$		-0.35	-0.60	V
Transition frequency	$f_T$	$V_{CB} = -10 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		120		MHz
Collector output capacitance (Common base, input open circuited)	C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		3.5	15.0	pF

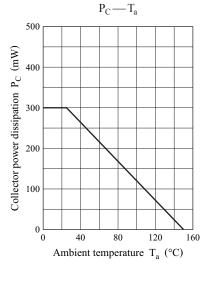
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

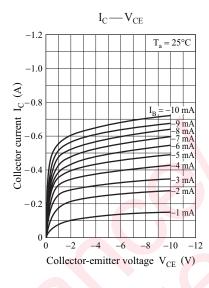
#### 2. \*: Rank classification

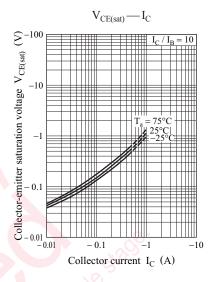
Rank	Q	R	S
$h_{\mathrm{FE1}}$	85 to 170	120 to 240	170 to 340

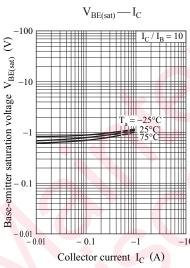
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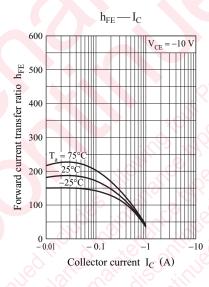
**Panasonic** 

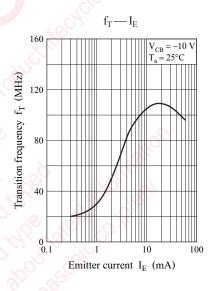


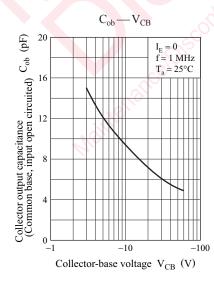


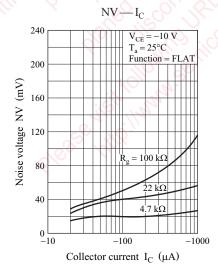








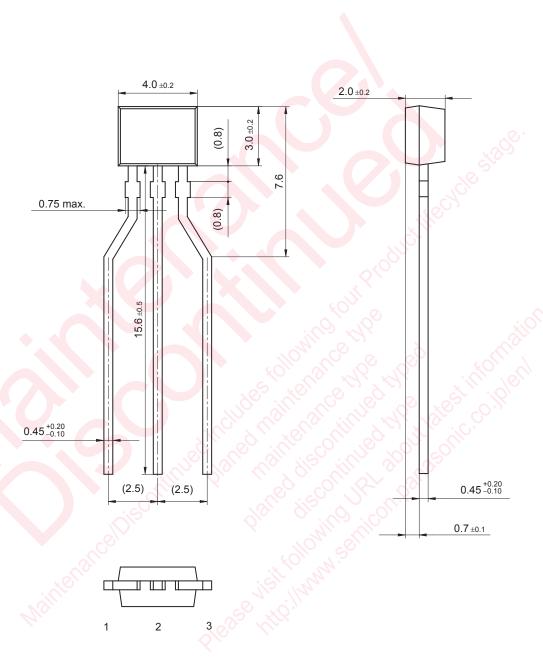




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Panasonic 2SB1030A

NS-B1 Unit: mm



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